

FDC640P

August 2000



SEMICONDUCTOR IM

FDC640P

P-Channel 2.5V Specified PowerTrench[™] MOSFET

General Description

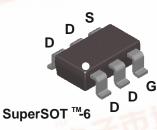
This P-Channel 2.5V specified MOSFET is produced in a rugged gate version of Fairchild Semiconductor's advanced PowerTrench process. It has been optimized for power management applications for a wide range of gate drive voltages.

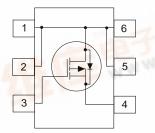
Applications

- Load switch
- Battery protection
- Power management

Features

- -4.5 A, -20 V. $R_{DS(ON)} = 0.050 \Omega @ V_{GS} = -4.5 V$ $R_{DS(ON)} = 0.077 \Omega @ V_{GS} = -2.5 V$
- Rugged gate rating (±12V).
- High performance trench technology for extremely low R_{DS(ON)}.
- SuperSOT[™]-6 package: small footprint (72% smaller than standard SO-8); low profile (1mm thick).





Absolute Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V _{DSS}	Drain-Source Voltage		-20	V
V _{GSS}	Gate-Source Voltage		<u>+</u> 12	V
I _D	Drain Current - Continuous	(Note 1a)	-4.5	A
	Drain Current - Pulsed		-20	1.0 1.0 -
PD	Power Dissipation for Single Operation	(Note 1a)	1.6	W
		(Note 1b)	0.8	
T _J , T _{stg}	Operating and Storage Junction Temperature Range		-55 to +150	∘C

R_{BJA} Thermal Resistance, Junction-to-Ambient (Note 1a) 78 °C/W R_{BJC} Thermal Resistance, Junction-to-Case (Note 1) 30 °C/W

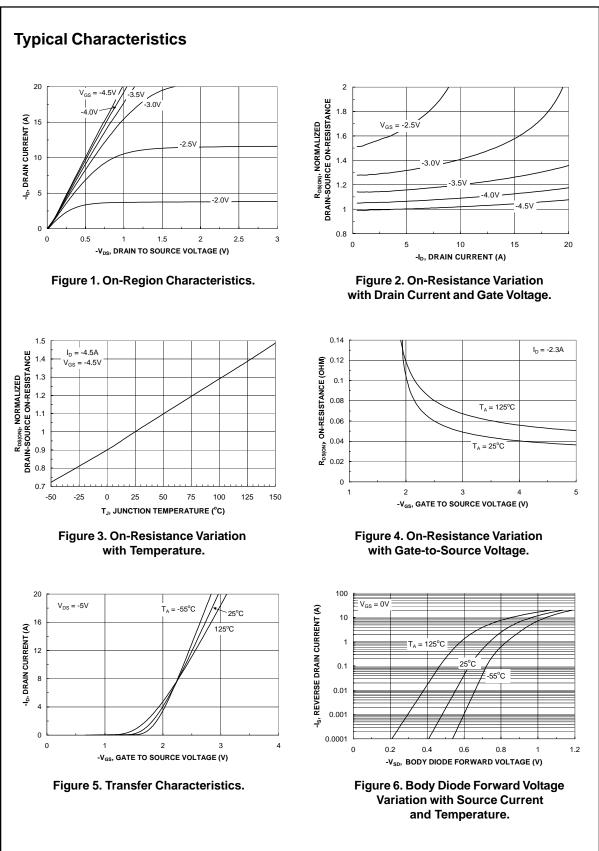
Package Outlines and Ordering Information

Device Marking	Device	Reel Size	Tape Width	Quantity
.640	FDC640P	7"	8mm	3000 units

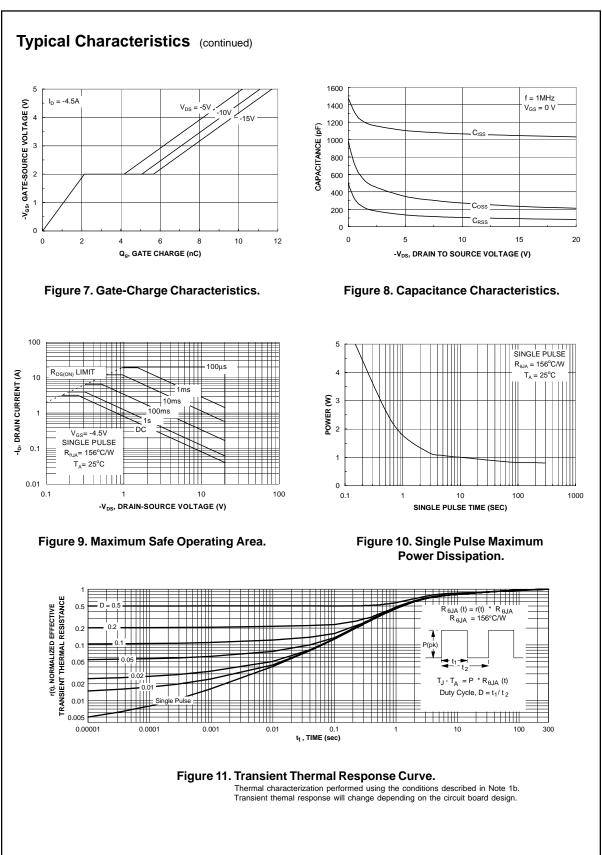
Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Cha	acteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, \text{ I}_{D} = -250 \mu\text{A}$	-20			V
	Breakdown Voltage Temperature Coefficient	$I_D = -250 \ \mu\text{A}$, Referenced to 25°C		-17		mV/∘C
DSS	Zero Gate Voltage Drain Current	$V_{DS} = -16 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$			-1	μA
GSSF	Gate-Body Leakage Current, Forward	V _{GS} = 12 V, V _{DS} = 0 V			100	nA
GSSR	Gate-Body Leakage Current, Reverse	V _{GS} = -12 V, V _{DS} = 0 V			-100	nA
On Char	acteristics (Note 2)					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \ \mu A$	-0.6	-1	-1.5	V
<u>Δ</u> VGS(th) ΔT,J	Gate Threshold Voltage Temperature Coefficient	$I_D = -250 \ \mu$ A, Referenced to 25°C		3		mV/∘C
R _{DS(on)}	Static Drain-Source On-Resistance	$V_{GS} = -4.5 V$, $I_D = -4.5 A$ $V_{GS} = -4.5V$, $I_D = -4.5A$, $T_J=125^{\circ}C$ $V_{GS} = -2.5 V$, $I_D = -3.6 A$		0.037 0.054 0.060	0.05 0.08 0.077	Ω
I _{D(on)}	On-State Drain Current	$V_{GS} = -4.5 \text{ V}, V_{DS} = -5 \text{ V}$	-10			А
9 _{FS}	Forward Transconductance	$V_{DS} = -5 V, I_{D} = -4.5 A$		13		S
Dynamio	Characteristics		•	•		
C _{iss}	Input Capacitance	$V_{DS} = -25 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1.0 MHz		1065		pF
Coss	Output Capacitance			270		pF
C _{rss}	Reverse Transfer Capacitance			105		pF
						·
	Turn-On Delay Time	$V_{DD} = -10 \text{ V}, \text{ I}_{D} = -1 \text{ A},$		8.5	17	ns
t _r	Turn-On Rise Time	$V_{GS} = -4.5 \text{ V}, \text{ R}_{GEN} = 6 \Omega$		10	18	ns
t _{d(off)}	Turn-Off Delay Time			55	90	ns
t _f	Turn-Off Fall Time			25	40	ns
Q _g	Total Gate Charge	$V_{DS} = -10 \text{ V}, \text{ I}_{D} = -4.5 \text{ A},$		10	14	nC
Q _{gs}	Gate-Source Charge	$V_{GS} = -4.5 V,$		2.1		nC
Q _{gd}	Gate-Drain Charge			2.9		nC
0		<u> </u>		2.0		
	Durce Diode Characteristics and Maximum Continuous Drain-Source Did				12	٨
s				0.75	-1.3	A V
V _{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0 V, I_S = -1.3 A$ (Note 2)		-0.75	-1.2	V

b) 156°C/W when mounted on a minimum pad.

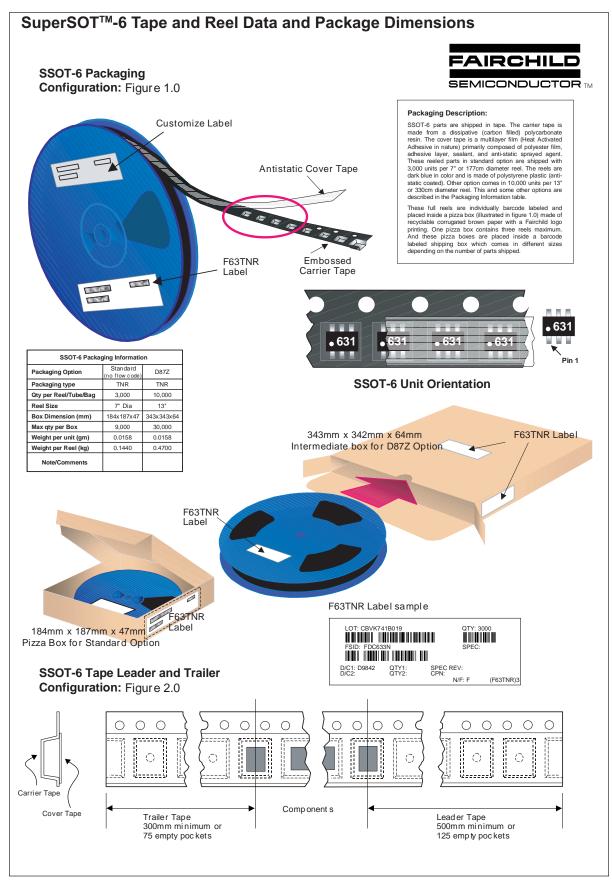
2. Pulse Test: Pulse Width \leq 300 µs, Duty Cycle \leq 2.0%

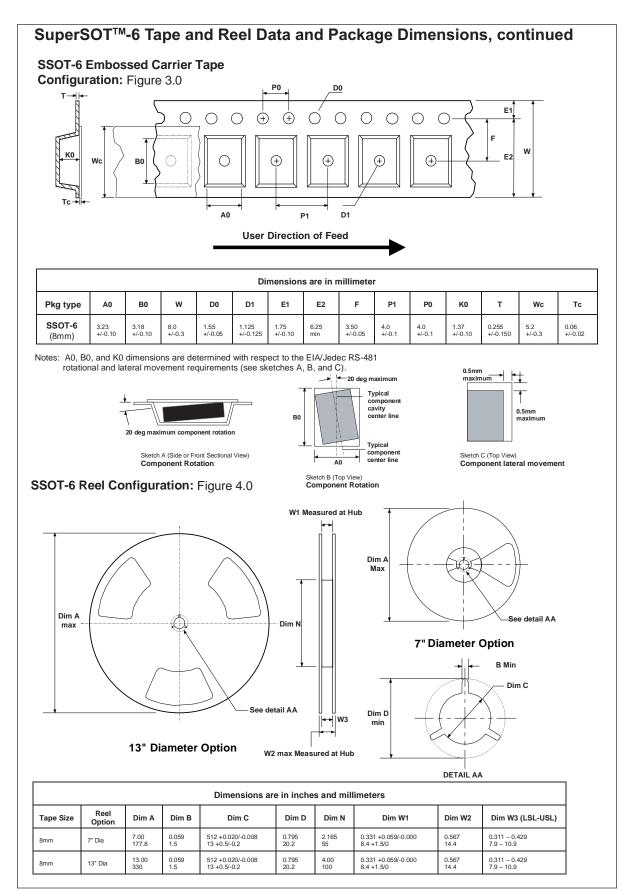


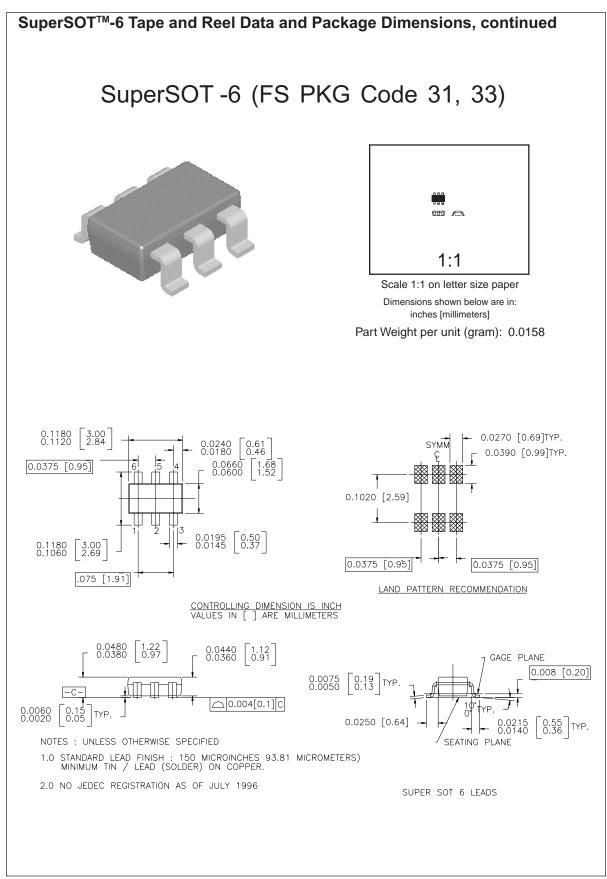
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FAST®	Powerirench®	UHC™	

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